

Silicon NPN Power Transistors

2SC1295

DESCRIPTION

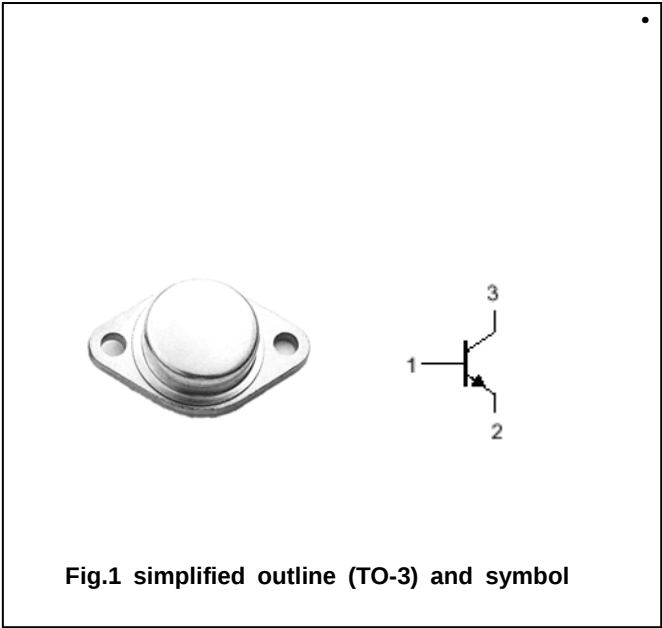
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- For TV horizontal deflection output applications

PINNING(see fig.2)

| PIN | DESCRIPTION |
|-----|-------------|
| 1   | Base        |
| 2   | Emitter     |
| 3   | Collector   |



Absolute maximum ratings(Ta=℃)

| SYMBOL           | PARAMETER                 | CONDITIONS          | VALUE   | UNIT |
|------------------|---------------------------|---------------------|---------|------|
| V <sub>CBO</sub> | Collector-base voltage    | Open emitter        | 1000    | V    |
| V <sub>CEO</sub> | Collector-emitter voltage | Open base           | 350     | V    |
| V <sub>EBO</sub> | Emitter-base voltage      | Open collector      | 5       | V    |
| I <sub>C</sub>   | Collector current         |                     | 2       | A    |
| P <sub>T</sub>   | Total power dissipation   | T <sub>C</sub> =25℃ | 40      | W    |
| T <sub>j</sub>   | Junction temperature      |                     | 150     | ℃    |
| T <sub>stg</sub> | Storage temperature       |                     | -55~150 | ℃    |

**Silicon NPN Power Transistors****2SC1295****CHARACTERISTICS****T<sub>j</sub>=25°C unless otherwise specified**

| SYMBOL                | PARAMETER                            | CONDITIONS                                 | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|--------------------------------------------|-----|------|-----|------|
| V <sub>CEO(SUS)</sub> | Collector-emitter sustaining voltage | I <sub>C</sub> =100mA; I <sub>B</sub> =0   | 350 |      |     | V    |
| V <sub>(BR)EBO</sub>  | Emitter-base breakdown voltage       | I <sub>E</sub> =1mA; I <sub>C</sub> =0     | 5   |      |     | V    |
| V <sub>CEsat</sub>    | Collector-emitter saturation voltage | I <sub>C</sub> =2 A; I <sub>B</sub> =1A    |     |      | 5.0 | V    |
| V <sub>BEsat</sub>    | Base-emitter saturation voltage      | I <sub>C</sub> =2 A; I <sub>B</sub> =1A    |     |      | 1.5 | V    |
| I <sub>CBO</sub>      | Collector cut-off current            | V <sub>CB</sub> =1000V; I <sub>E</sub> =0  |     |      | 0.1 | mA   |
| I <sub>EBO</sub>      | Emitter cut-off current              | V <sub>EB</sub> =5V; I <sub>C</sub> =0     |     |      | 0.1 | mA   |
| h <sub>FE</sub>       | DC current gain                      | I <sub>C</sub> =1.5A ; V <sub>CE</sub> =5V | 3   |      | 13  |      |

## PACKAGE OUTLINE

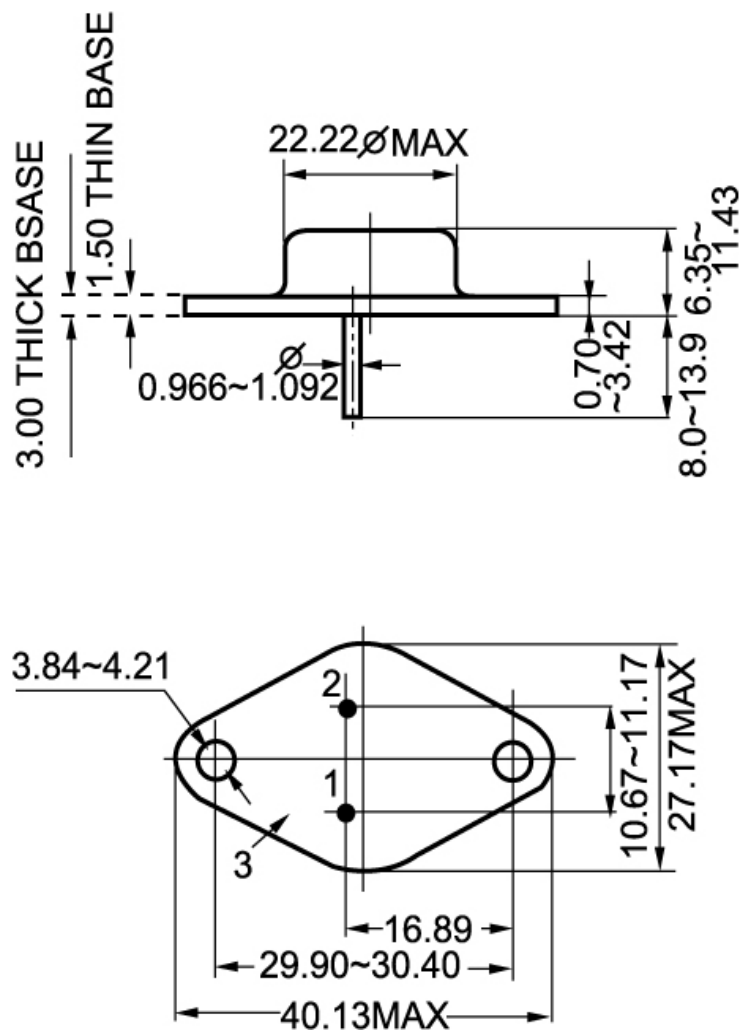


Fig.2 Outline dimensions